

U.S.S.N. 10,656,986

Claim Amendments

Please amend claims 1, 6, and 14-19 as follows:

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Listing of Claims

1. (currently amended) A method for exposing a blanket photoresist layer comprising:

providing a substrate having formed thereover a photoresist layer; and

exposing within a single die region within the photoresist layer a minimum of two non-overlapping die sub-patterns while employing a minimum of two masks, each of said masks associated with one of said non-overlapping die sub-patterns.

2. (original) The method of claim 1 wherein the substrate is a semiconductor substrate.

3. (original) The method of claim 1 wherein the substrate is a ceramic substrate.

4. (original) The method of claim 1 wherein the blanket photoresist layer is formed of a positive photoresist material.

5. (original) The method of claim 1 wherein the blanket

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photoresist layer is formed of a negative photoresist material.

6. (currently amended) A method for exposing a photoresist layer comprising:

providing a substrate having formed thereover a photoresist layer; and

exposing within a single die region within the photoresist layer a minimum of two non-overlapping die sub-patterns while employing a minimum of two masks and two exposure conditions, each of said masks associated with one of said non-overlapping die sub-patterns.

7. (original) The method of claim 6 wherein the substrate is a semiconductor substrate.

8. (original) The method of claim 6 wherein the substrate is a ceramic substrate.

9. (original) The method of claim 6 wherein the photoresist layer is formed of a positive photoresist material.

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10. (original) The method of claim 6 wherein the photoresist layer is formed of a negative photoresist material.

11. (original) The method of claim 6 wherein the exposure conditions include exposure energy.

12. (original) The method of claim 6 wherein the exposure conditions include depth of focus.

13. (original) The method of claim 6 wherein the exposure conditions include illumination.

14. (currently amended) A method for forming a patterned layer comprising:

providing a substrate having formed thereover a target layer having formed thereover a photoresist layer;

exposing within a single die region within the photoresist layer a minimum of two non-overlapping die sub-patterns while employing a minimum of two masks, to form an exposed photoresist layer, each of said masks associated with one of said non-overlapping die sub-patterns;

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developing the exposed photoresist layer to form a patterned photoresist layer; and

processing the target layer to form a processed target layer while employing the patterned photoresist layer as a mask layer.

15. (currently amended) The method of claim 14 wherein the substrate is a semiconductor substrate.

16. (currently amended) The method of claim 14 wherein the substrate is a ceramic substrate.

17. (currently amended) The method of claim 14 wherein the blanket photoresist layer is formed of a positive photoresist material.

18. (currently amended) The method of claim 14 wherein the blanket photoresist layer is formed of a negative photoresist material.

19. (currently amended) The method of claim 14 wherein the exposing of the photoresist layer employing two masks also

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employs at least two separate exposure conditions.

20. (original) The method of claim 19 wherein the separate exposure conditions are selected from the group including exposure energy, depth of focus and illumination.

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